

Inchange Semiconductor

Product Specification

Silicon NPN Power Transistors

2SC1358

DESCRIPTION

- With TO-3 package
- High breakdown voltage
- High speed switching

APPLICATIONS

- Designed for use in large screen color deflection circuits

PINNING (See Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector



Absolute maximum ratings(Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	1400	V
V _{CEO}	Collector-emitter voltage	Open base	500	V
V _{EBO}	Emitter-base voltage	Open collector	6	V
I _C	Collector current		4.5	A
I _{CM}	Collector current-peak		10	A
I _B	Base current		1.5	A
P _T	Total power dissipation	T _C =25°C	50	W
T _j	Junction temperature		150	°C
T _{stg}	Storage temperature		-65~150	°C

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
R _{th j-c}	Thermal resistance from junction to case	2.5	°C/W

Silicon NPN Power Transistors

2SC1358

CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEO(SUS)}	Collector-emitter sustaining voltage	I _C =0.1A ; I _B =0	500			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =4A; I _B =0.8A			10	V
V _{BEsat}	Base-emitter saturation voltage	I _C =4A; I _B =0.8A			1.2	V
I _{CES}	Collector cut-off current	V _{CE} =1400V; V _{BE} =0			1.0	mA
I _{CBO}	Collector cut-off current	V _{CB} =1000V; I _E =0			20	μ A
I _{EBO}	Emitter cut-off current	V _{EB} =5V; I _C =0			200	μ A
h _{FE-1}	DC current gain	I _C =0.5A ; V _{CE} =15V	10		45	
h _{FE-2}	DC current gain	I _C =3A ; V _{CE} =15V	5		35	
t _{stg}	Storage time	I _C =4A; I _{B1} =-I _{B2} =1.0A P _W =20 μ s			10	μ s
t _f	Fall time				1.0	μ s

Silicon NPN Power Transistors

2SC1358

PACKAGE OUTLINE

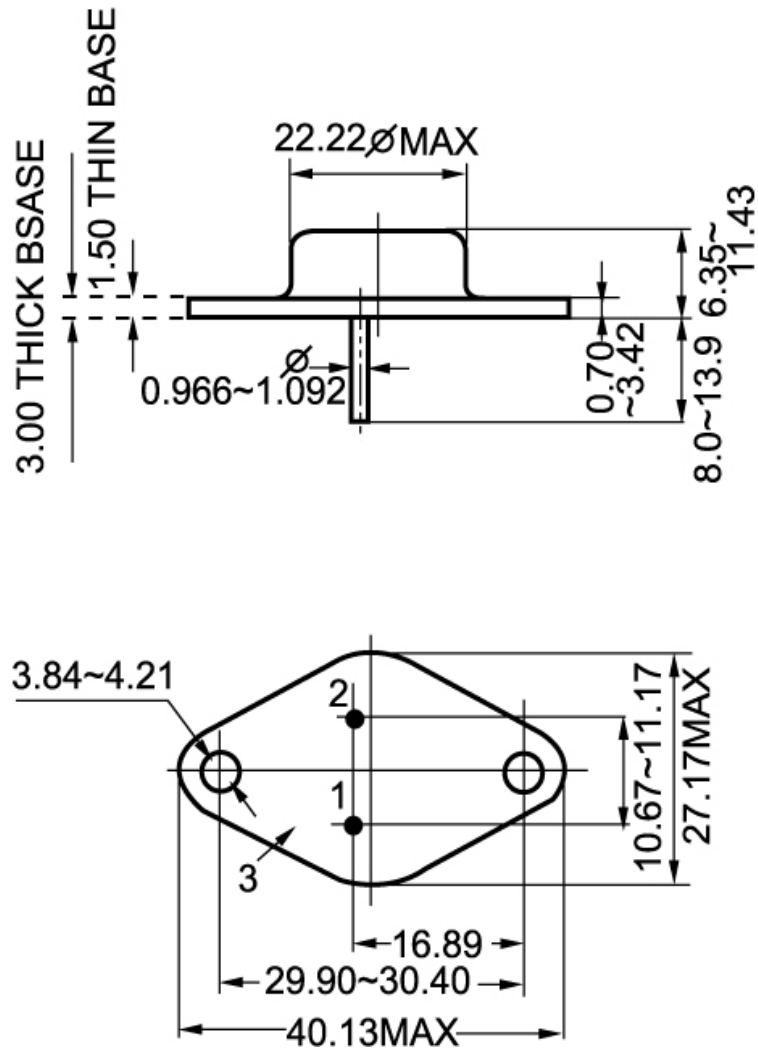


Fig.2 Outline dimensions